

**Vishay Siliconix** 

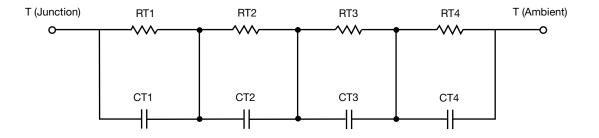
## **R-C Thermal Model Parameters**

#### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	N/A	663.4850m	N/A		
RT2	N/A	978.2022m	N/A		
RT3	N/A	892.0991m	N/A		
RT4	N/A	466.2136m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	345.4697m	N/A		
CT2	N/A	871.7936u	N/A		
CT3	N/A	14.2905m	N/A		
CT4	N/A	21.6626m	N/A		

Note

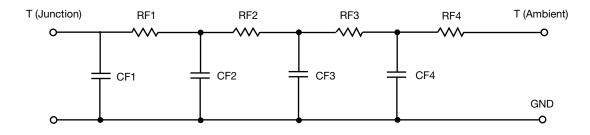
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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## **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	N/A	1.2772	N/A		
RF2	N/A	1.0287	N/A		
RF3	N/A	444.3855m	N/A		
RF4	N/A	251.9742m	N/A		
·	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	866.3629u	N/A		
CF2	N/A	10.0659m	N/A		
CF3	N/A	154.7390m	N/A		
CF4	N/A	1.9131	N/A		

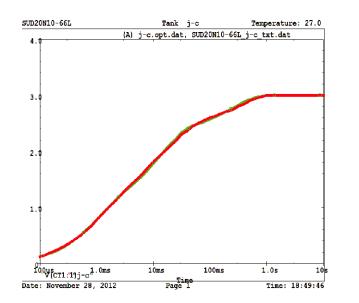
Note

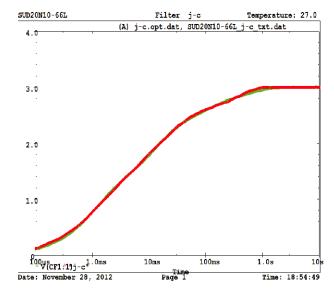
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# SUD20N10-66L\_RC

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Revision: 28-Nov-12